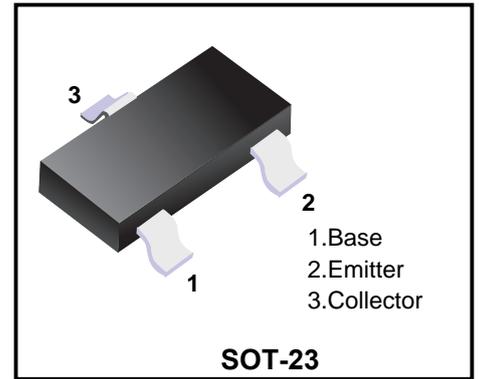


NPN Silicon AF and Switching Transistors

- For general AF applications
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary types: BCX42, BSS63 (PNP)



Type	Marking	Pin Configuration			Package
BCX41	EKs	1 = B	2 = E	3 = C	SOT23
BSS64	AMs	1 = B	2 = E	3 = C	SOT23

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	BSS64	BCX41	Unit
Collector-emitter voltage	V_{CEO}	80	125	V
Collector-base voltage	V_{CBO}	120	125	
Emitter-base voltage	V_{EBO}	5	5	
DC collector current	I_C	800		mA
Peak collector current	I_{CM}	1		A
Base current	I_B	100		mA
Peak base current	I_{BM}	200		
Total power dissipation, $T_S = 79\text{ °C}$	P_{tot}	330		mW
Junction temperature	T_j	150		°C
Storage temperature	T_{stg}	-65 ... 150		

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	215	K/W
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¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics (Ta=25°C unless otherwise specified.)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$	BSS64 BCX41	$V_{(BR)CEO}$	80 125	- -	- -	V
Collector-base breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	BSS64 BCX41	$V_{(BR)CBO}$	120 125	- -	- -	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$		$V_{(BR)EBO}$	5	-	-	
Collector cutoff current $V_{CB} = 80 \text{ V}, I_E = 0$ $V_{CB} = 100 \text{ V}, I_E = 0$	BSS64 BCX41	I_{CBO}	- -	- -	100 100	nA
Collector cutoff current $V_{CB} = 80 \text{ V}, I_E = 0, T_A = 150 \text{ }^\circ\text{C}$ $V_{CB} = 100 \text{ V}, I_E = 0, T_A = 150 \text{ }^\circ\text{C}$	BSS64 BCX41	I_{CBO}	- -	- -	20 20	μA
Emitter cutoff current $V_{EB} = 4 \text{ V}, I_C = 0$		I_{EBO}	-	-	100	nA
Collector cutoff current $V_{CE} = 100 \text{ V}, T_A = 85 \text{ }^\circ\text{C}$ $V_{CE} = 100 \text{ V}, T_A = 125 \text{ }^\circ\text{C}$	BCX41 BCX41	I_{CEO}	- -	- -	10 75	μA
DC current gain 1) $I_C = 100 \mu\text{A}, V_{CE} = 1 \text{ V}$ $I_C = 1 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 4 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 20 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_C = 200 \text{ mA}, V_{CE} = 1 \text{ V}$	BCX41 BSS64 BSS64 BSS64 BSS64 BCX41 BCX41	h_{FE}	25 - 20 - - 63 40	- 60 80 80 55 - -	- - - - - - -	-

 1) Pulse test: $t \leq 300 \mu\text{s}$, $D = 2\%$

Electrical Characteristics (Ta=25°C unless otherwise specified.)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

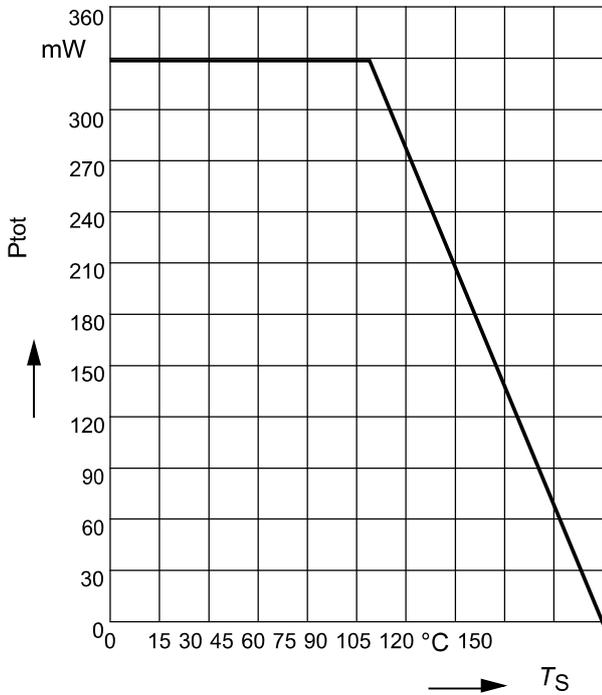
DC Characteristics

Collector-emitter saturation voltage 1) $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ BCX41	V_{CEsat}	-	-	0.9	V
$I_C = 4 \text{ mA}, I_B = 0.4 \text{ mA}$ BSS64		-	-	0.7	
$I_C = 50 \text{ mA}, I_B = 15 \text{ mA}$ BSS64		-	-	3	
Base-emitter saturation voltage 1) $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ BCX41	V_{BEsat}	-	-	1.4	

AC Characteristics

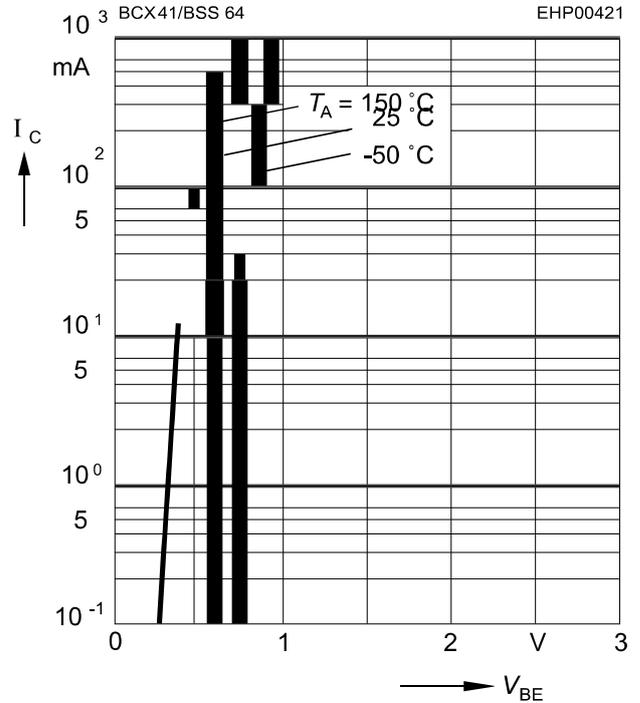
Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 20 \text{ MHz}$	f_T	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	12	-	pF

Total power dissipation $P_{tot} = f(T_S)$



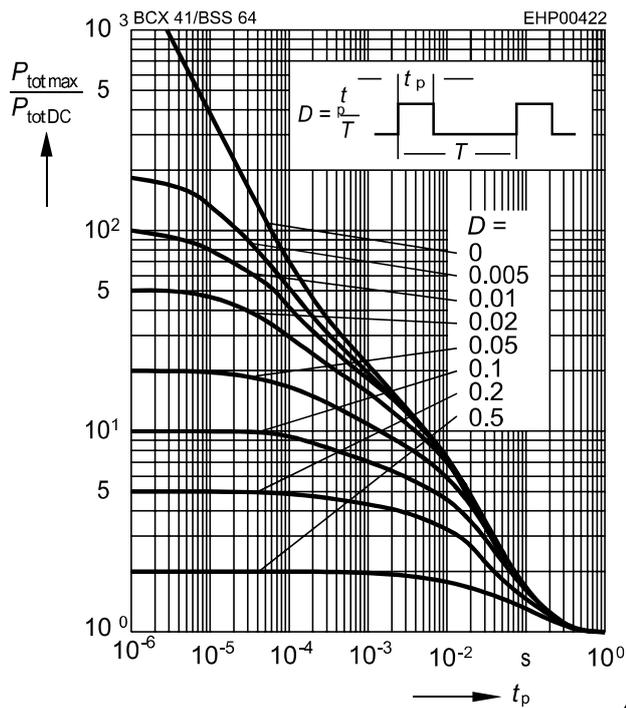
Collector current $I_C = f(V_{BE})$

$V_{CE} = 1V$



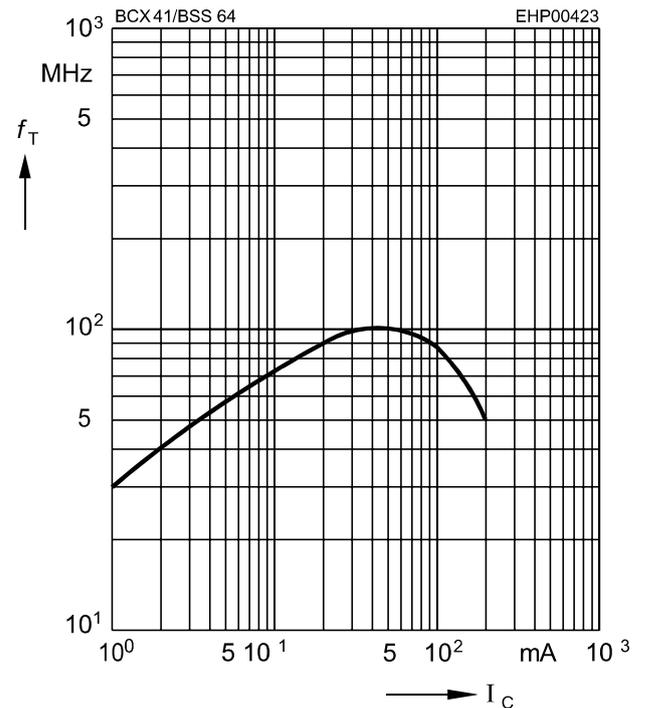
Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$



Transition frequency $f_T = f(I_C)$

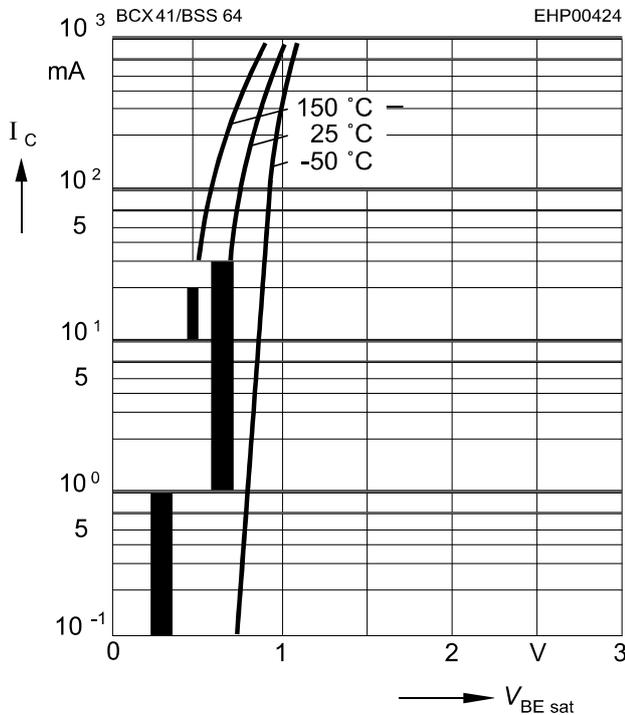
$V_{CE} = 5V$



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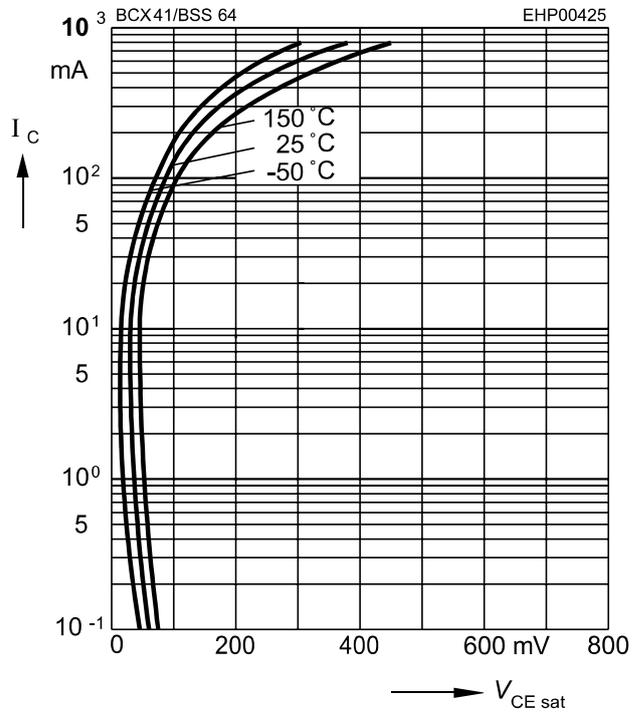
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



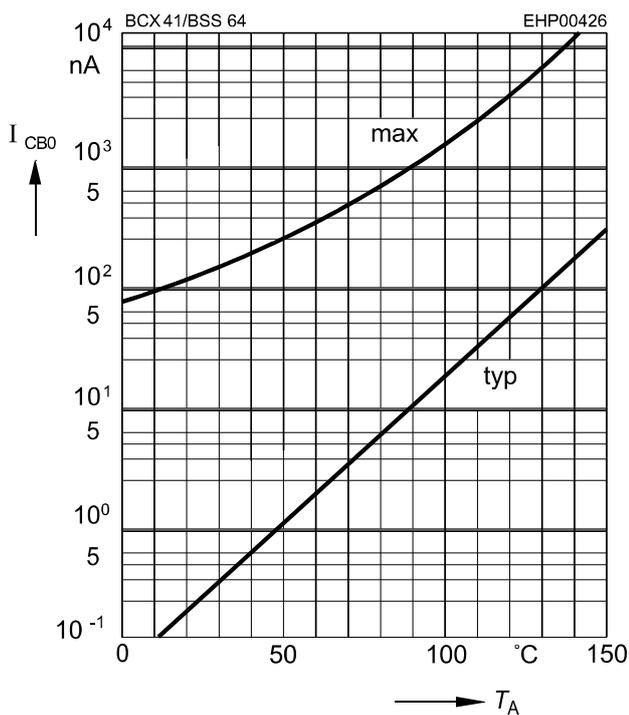
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



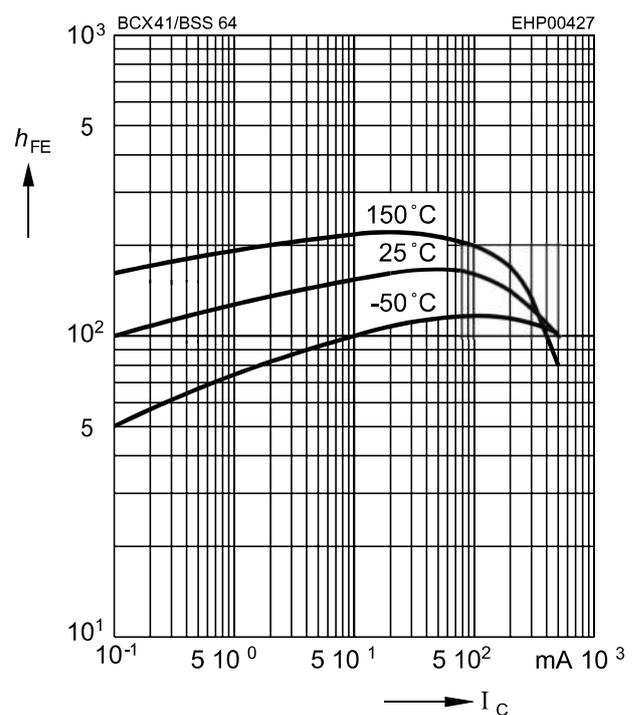
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = 80V$



DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1V$



Ordering information

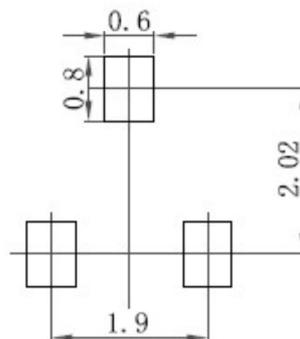
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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